

isc N-Channel MOSFET Transistor

AOT11S65

FEATURES

- Drain Current –I_D=11A@ T_C=25 $^\circ\!\!\mathrm{C}$
- Drain Source Voltage-: V_{DSS}=650V(Min)
- Static Drain-Source On-Resistance
- : $R_{DS(on)} = 0.399 \Omega$ (Max)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

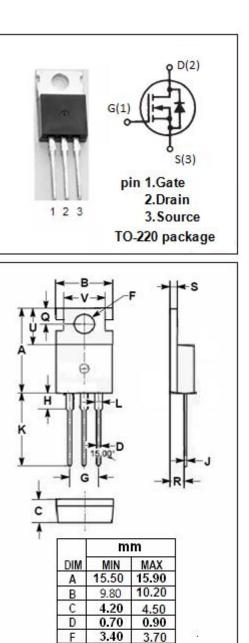
• Designed for use in switch mode power supplies and general purpose applications.

| SYMBOL | PARAMETER | VALUE | UNIT | | | | |
|------------------|---|-------|------|--|--|--|--|
| V _{DSS} | Drain-Source Voltage | 650 | V | | | | |
| V _{GS} | Gate-Source Voltage-Continuous | ±30 | V | | | | |
| ID | Drain Current-Continuous | 11 | A | | | | |
| I _{DM} | Drain Current-Single Pluse | 45 | A | | | | |
| P _D | Total Dissipation @T _c =25℃ | 198 | w | | | | |
| TJ | Max. Operating Junction Temperature -55~150 | | °C | | | | |
| T _{stg} | Storage Temperature -55~150 | | °C | | | | |

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------------|--------------------------------------|------|------|
| R _{th j-c} | Thermal Resistance, Junction to Case | 0.63 | °C/W |



¹ *isc & iscsemi* is registered trademark

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4.98

2.68

0.44

12.80

1.20

2.70

2.30

1.29

6.45

8.66

5.18

2.90

0.60

13.40

1.45

2.90

2.70

1.35

6.65

8.86

isc website: <u>www.iscsemi.com</u>



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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

| SYMBO L | PARAMETER | CONDITIONS | MIN | TYPE | МАХ | UNIT |
|----------------------|---------------------------------|---|-----|------|-------|------|
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0; I _D = 0.25mA | 650 | | | V |
| $V_{GS(th)}$ | Gate Threshold Voltage | V _{DS} = 5V; I _D = 0.25mA | 2.6 | | 4.0 | V |
| $R_{\text{DS(on)}}$ | Drain-Source On-Resistance | V _{GS} = 10V; I _D = 5.5A | | | 0.399 | Ω |
| I _{GSS} | Gate-Body Leakage Current | V _{GS} = ±30V;V _{DS} = 0 | | | ±100 | nA |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 650V; V _{GS} = 0 | | | 1 | μA |
| Vsd | Forward On-Voltage | I _S = 5.5A; V _{GS} = 0 | | 0.82 | | V |

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